

Erratum

Oxidation kinetics of hot-pressed silicon carbide

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J. Mater. Sci. 11 (1976) 1246–1253.

Figure 5, page 1250, was incorrectly printed. The correct version is given below.

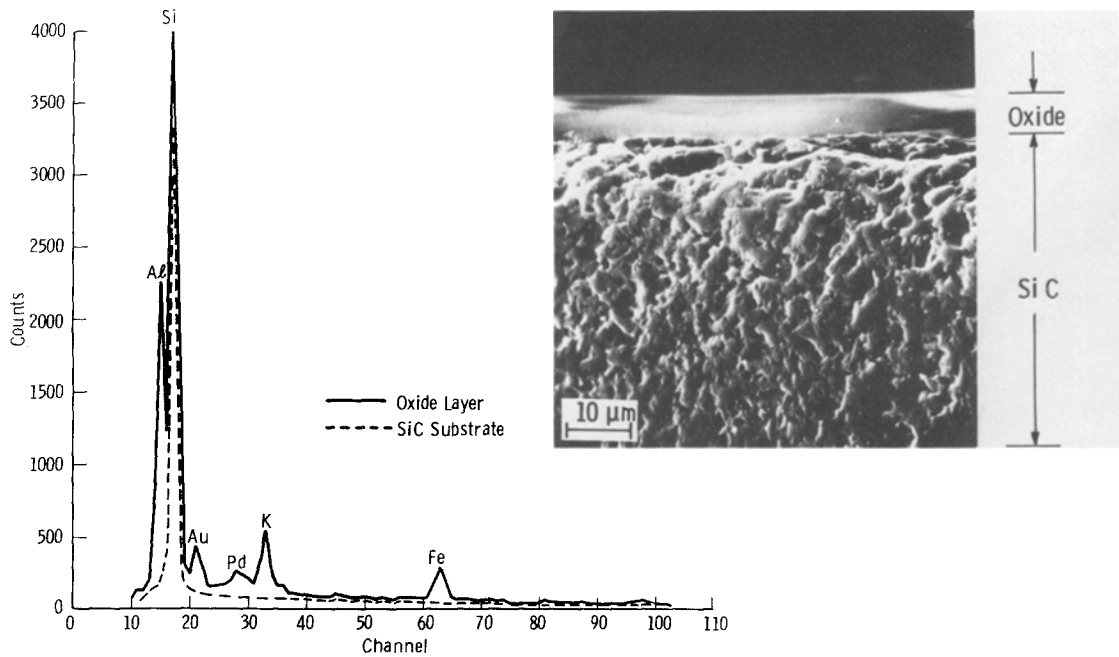


Figure 5 Scanning electron micrograph of the transverse section of a SiC specimen oxidized at 1370° C for 1203 h with energy dispersive X-ray analysis in the oxide layer and in the SiC substrate.